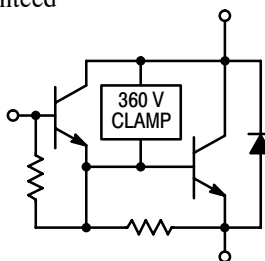


# NPN Silicon Power Darlington High Voltage Autoprotected

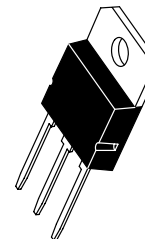
The BU323Z is a planar, monolithic, high-voltage power Darlington with a built-in active zener clamping circuit. This device is specifically designed for unclamped, inductive applications such as Electronic Ignition, Switching Regulators and Motor Control, and exhibit the following main features:

- Integrated High-Voltage Active Clamp
- Tight Clamping Voltage Window (350 V to 450 V) Guaranteed Over the -40°C to +125°C Temperature Range
- Clamping Energy Capability 100% Tested in a Live Ignition Circuit
- High DC Current Gain/Low Saturation Voltages Specified Over Full Temperature Range
- Design Guarantees Operation in SOA at All Times
- Offered in Plastic SOT-93/TO-218 Type or TO-220 Packages
- **This device is available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at [www.onsemi.com](http://www.onsemi.com) for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.**



**BU323Z**

**AUTOPROTECTED  
DARLINGTON  
10 AMPERES  
360-450 VOLTS CLAMP  
150 WATTS**



**CASE 340D-02  
SOT-93/TO-218 TYPE**

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	$V_{CEO}$	350	Vdc
Collector-Emitter Voltage	$V_{EBO}$	6.0	Vdc
Collector Current — Continuous — Peak	$I_C$ $I_{CM}$	10 20	Adc
Base Current — Continuous — Peak	$I_B$ $I_{BM}$	3.0 6.0	Adc
Total Power Dissipation Derate above 25°C	$P_D$	150 1.0	Watts W/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +175	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	$T_L$	260	°C

# BU323Z

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS (1)</b>					
Collector–Emitter Clamping Voltage ( $I_C = 7.0\text{ A}$ ) ( $T_C = -40^\circ\text{C}$ to $+125^\circ\text{C}$ )	$V_{\text{CLAMP}}$	350	—	450	Vdc
Collector–Emitter Cutoff Current ( $V_{\text{CE}} = 200\text{ V}$ , $I_B = 0$ )	$I_{\text{CEO}}$	—	—	100	$\mu\text{Adc}$
Emitter–Base Leakage Current ( $V_{\text{EB}} = 6.0\text{ Vdc}$ , $I_C = 0$ )	$I_{\text{EBO}}$	—	—	50	mAdc

## ON CHARACTERISTICS (1)

Base–Emitter Saturation Voltage ( $I_C = 8.0\text{ Adc}$ , $I_B = 100\text{ mAdc}$ ) ( $I_C = 10\text{ Adc}$ , $I_B = 0.25\text{ Adc}$ )	$V_{\text{BE(sat)}}$	— —	— —	2.2 2.5	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 7.0\text{ Adc}$ , $I_B = 70\text{ mAdc}$ )  ( $I_C = 8.0\text{ Adc}$ , $I_B = 0.1\text{ Adc}$ )  ( $I_C = 10\text{ Adc}$ , $I_B = 0.25\text{ Adc}$ )	$V_{\text{CE(sat)}}$	— — —	— — —	1.6 1.8 1.8 2.1 1.7	Vdc
Base–Emitter On Voltage ( $I_C = 5.0\text{ Adc}$ , $V_{\text{CE}} = 2.0\text{ Vdc}$ ) ( $I_C = 8.0\text{ Adc}$ , $V_{\text{CE}} = 2.0\text{ Vdc}$ )	$V_{\text{BE(on)}}$	1.1 1.3	— —	2.1 2.3	Vdc
Diode Forward Voltage Drop ( $I_F = 10\text{ Adc}$ )	$V_F$	—	—	2.5	Vdc
DC Current Gain ( $I_C = 6.5\text{ Adc}$ , $V_{\text{CE}} = 1.5\text{ Vdc}$ ) ( $I_C = 5.0\text{ Adc}$ , $V_{\text{CE}} = 4.6\text{ Vdc}$ )	$h_{\text{FE}}$	150 500	— —	— 3400	—

## DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ( $I_C = 0.2\text{ Adc}$ , $V_{\text{CE}} = 10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$f_T$	—	—	2.0	MHz
Output Capacitance ( $V_{\text{CB}} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{\text{ob}}$	—	—	200	pF
Input Capacitance ( $V_{\text{EB}} = 6.0\text{ V}$ )	$C_{\text{ib}}$	—	—	550	pF

## CLAMPING ENERGY (see notes)

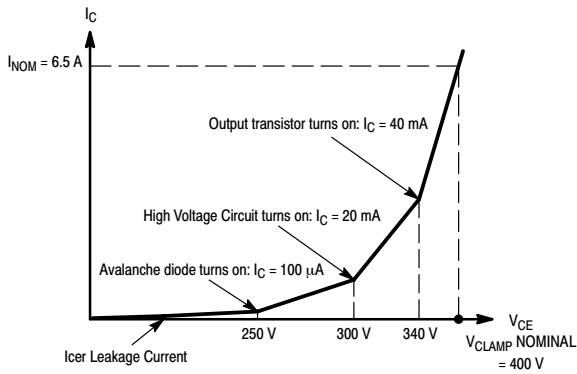
Repetitive Non–Destructive Energy Dissipated at turn–off: ( $I_C = 7.0\text{ A}$ , $L = 8.0\text{ mH}$ , $R_{\text{BE}} = 100\ \Omega$ ) (see Figures 2 and 4)	$W_{\text{CLAMP}}$	200	—	—	mJ
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## SWITCHING CHARACTERISTICS: Inductive Load ( $L = 10\text{ mH}$ )

Fall Time	$(I_C = 6.5\text{ A}$ , $I_{\text{B1}} = 45\text{ mA}$ , $V_{\text{BE(off)}} = 0$ , $R_{\text{BE(off)}} = 0$ , $V_{\text{CC}} = 14\text{ V}$ , $V_Z = 300\text{ V}$ )	$t_{\text{fi}}$	—	625	—	ns
Storage Time		$t_{\text{si}}$	—	10	30	$\mu\text{s}$
Cross–over Time		$t_c$	—	1.7	—	$\mu\text{s}$

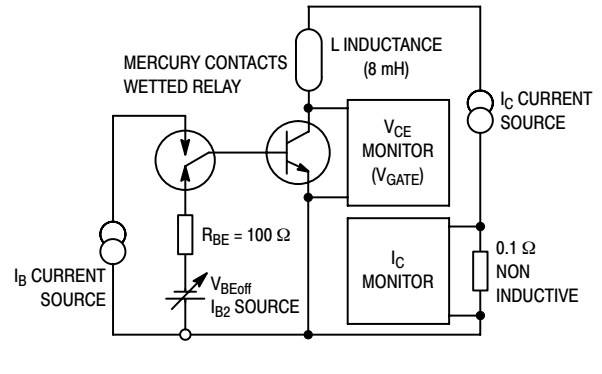
(1) Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle = 2.0%.

# BU323Z



**Figure 1.  $I_C = f(V_{CE})$  Curve Shape**

By design, the BU323Z has a built-in avalanche diode and a special high voltage driving circuit. During an auto-protect cycle, the transistor is turned on again as soon as a voltage, determined by the zener threshold and the network, is reached. This prevents the transistor from going into a Reverse Bias Operating limit condition. Therefore, the device will have an extended safe operating area and will always appear to be in "FBSOA." Because of the built-in zener and associated network, the  $I_C = f(V_{CE})$  curve exhibits an unfamiliar shape compared to standard products as shown in Figure 1.

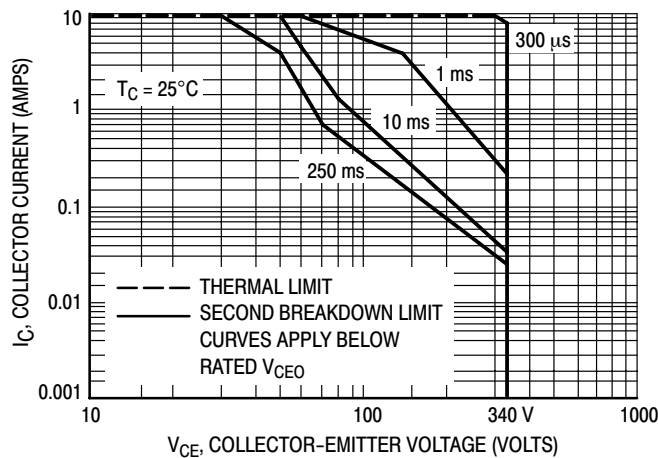


**Figure 2. Basic Energy Test Circuit**

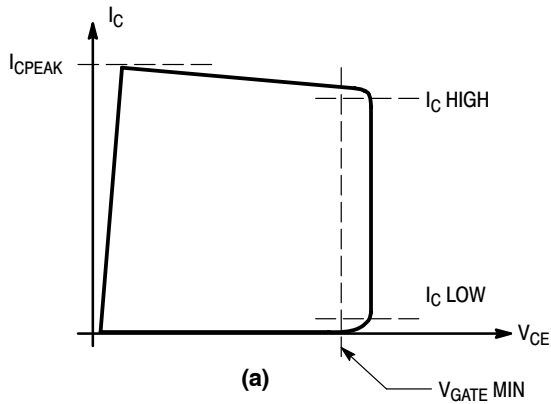
The bias parameters,  $V_{CLAMP}$ ,  $I_{B1}$ ,  $V_{BE(off)}$ ,  $I_{B2}$ ,  $I_C$ , and the inductance, are applied according to the Device Under Test (DUT) specifications.  $V_{CE}$  and  $I_C$  are monitored by the test system while making sure the load line remains within the limits as described in Figure 4.

Note: All BU323Z ignition devices are 100% energy tested, per the test circuit and criteria described in Figures 2 and 4, to the minimum guaranteed repetitive energy, as specified in the device parameter section. The device can sustain this energy on a repetitive basis without degrading any of the specified electrical characteristics of the devices. The units under test are kept functional during the complete test sequence for the test conditions described:

$I_{C(peak)} = 7.0 \text{ A}$ ,  $I_{CH} = 5.0 \text{ A}$ ,  $I_{CL} = 100 \text{ mA}$ ,  $I_B = 100 \text{ mA}$ ,  $R_{BE} = 100 \text{ } \Omega$ ,  $V_{gate} = 280 \text{ V}$ ,  $L = 8.0 \text{ mH}$

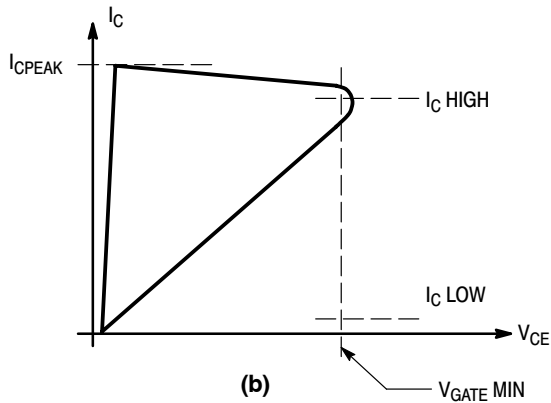


**Figure 3. Forward Bias Safe Operating Area**

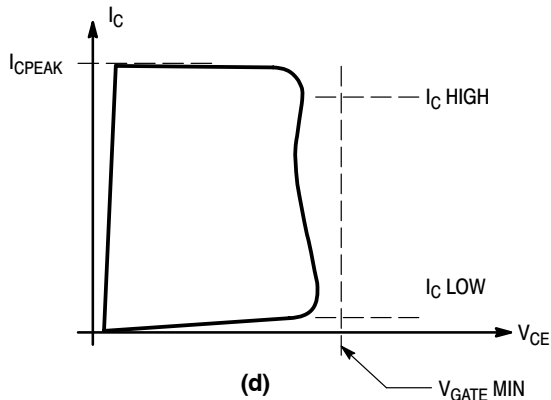
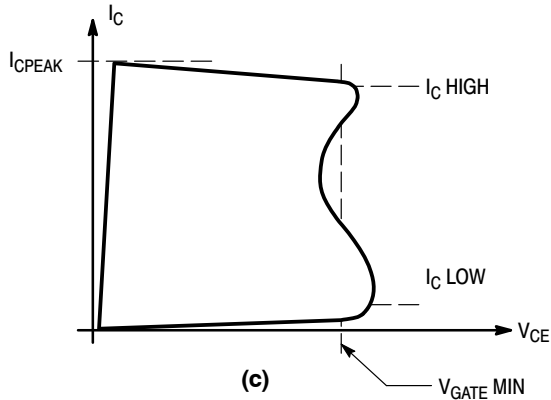


The shaded area represents the amount of energy the device can sustain, under given DC biases ( $I_C/I_B/V_{BE(off)}/R_{BE}$ ), without an external clamp; see the test schematic diagram, Figure 2.

The transistor PASSES the Energy test if, for the inductive load and  $I_{CPEAK}/I_B/V_{BE(off)}$  biases, the  $V_{CE}$  remains outside the shaded area and greater than the  $V_{GATE}$  minimum limit, Figure 4a.



The transistor FAILS if the  $V_{CE}$  is less than the  $V_{GATE}$  (minimum limit) at any point along the  $V_{CE}/I_C$  curve as shown on Figures 4b, and 4c. This assures that hot spots and uncontrolled avalanche are not being generated in the die, and the transistor is not damaged, thus enabling the sustained energy level required.



The transistor FAILS if its Collector/Emitter breakdown voltage is less than the  $V_{GATE}$  value, Figure 4d.

Figure 4. Energy Test Criteria for BU323Z

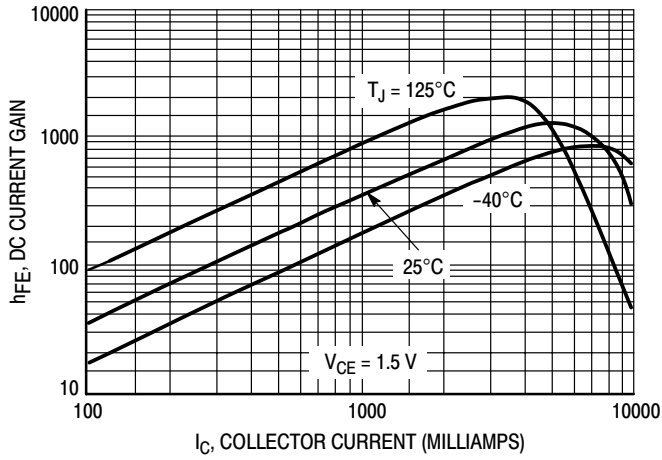


Figure 5. DC Current Gain

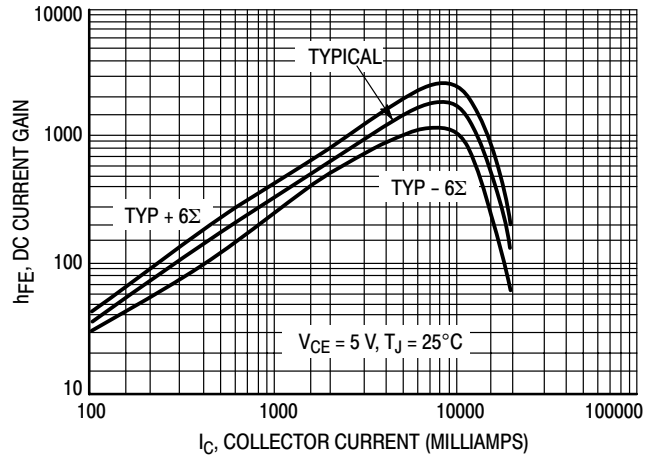


Figure 6. DC Current Gain

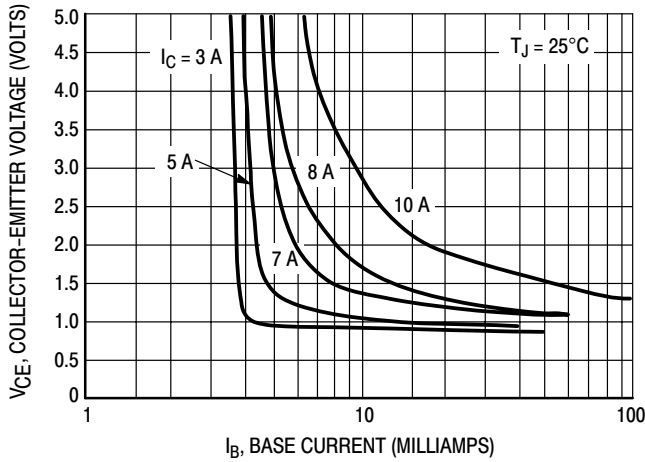


Figure 7. Collector Saturation Region

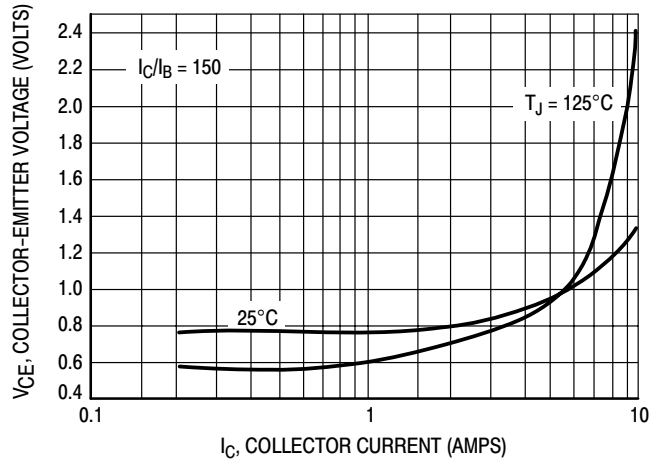


Figure 8. Collector-Emitter Saturation Voltage

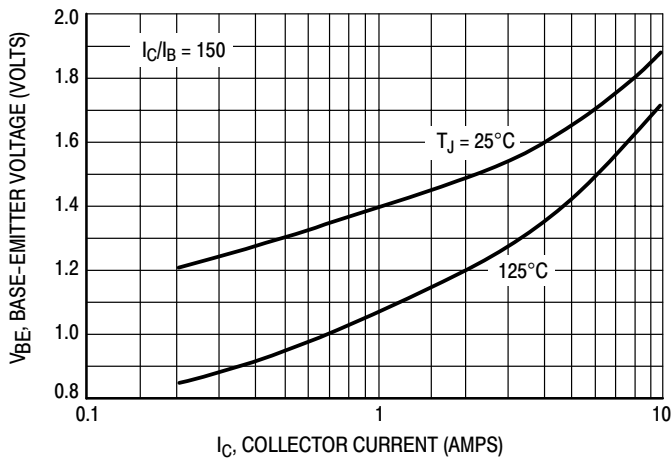


Figure 9. Base-Emitter Saturation Voltage

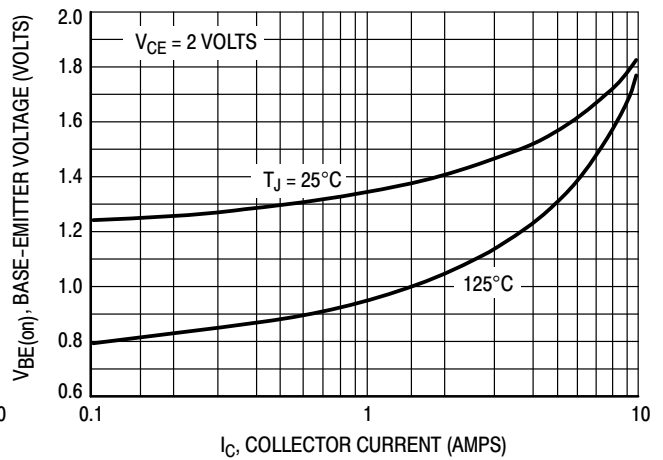
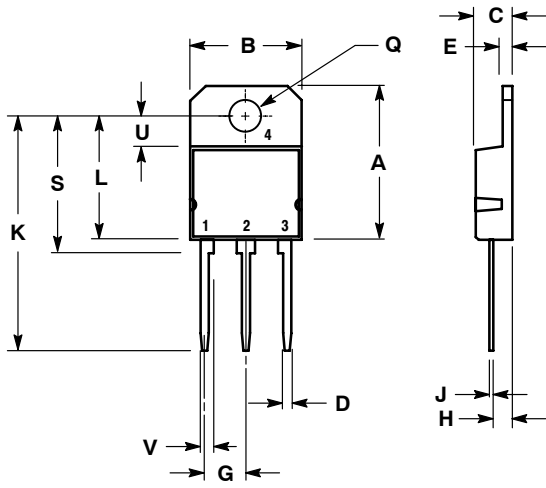


Figure 10. Base-Emitter "ON" Voltages

# BU323Z

## PACKAGE DIMENSIONS CASE 340D-02 SOT-93/TO-218 TYPE ISSUE E



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

# Notes

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